UTC UNISONIC TECHNOLOGIES CO., LTD

MJE13003D-XS

NPN SILICON TRANSISTOR

NPN SILICON POWER TRANSISTOR

DESCRIPTION

These devices are designed for high-voltage, high-speed power switching inductive circuits where fall time is critical. They are particularly suited for 115V and 220V applications in switch mode.

FEATURES

* 700V blocking capability

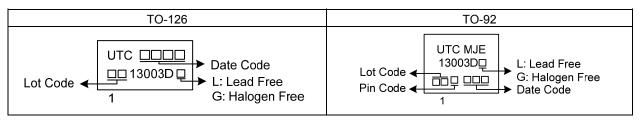
APPLICATIONS

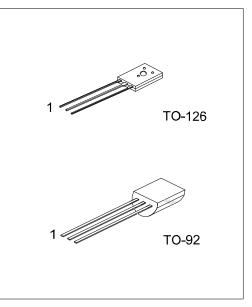
- * Switching regulator's, inverters
- * Motor controls
- * Solenoid/relay drivers
- * Deflection circuits

ORDERING INFORMATION

| Ordering | Deekege | Pin Assignment | | | Decking | | |
|---|-----------------------|----------------|---|---|---------|----------|--|
| Lead Free | Halogen-Free | Package | 1 | 2 | 3 | Packing | |
| MJE13003DL-XS-T60-K | MJE13003DG-XS-T60-K | TO-126 | В | С | Е | Bulk | |
| MJE13003DL-XS-92-A-B | MJE13003DG-XS-T92-A-B | TO-92 | Е | С | В | Tape Box | |
| MJE13003DL-XS-T92-A-K | MJE13003DG-XS-T92-A-K | TO-92 | Е | С | В | Bulk | |
| MJE13003DL-XS-92-F-B | MJE13003DG-XS-T92-F-B | TO-92 | В | С | Е | Tape Box | |
| MJE13003DL-XS-T92-F-K | MJE13003DG-XS-T92-F-K | TO-92 | В | С | Е | Bulk | |
| Note: Pin Assignment: B: Base C: Collector E: Emitter | | | | | | | |

■ MARKING





■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified.)

| PARAMETER | | SYMBOL | RATINGS | UNIT | |
|---------------------------|----------------------------|-----------------------|------------------|------------|----|
| Collector-Emitter Voltage | | V _{CEO(SUS)} | 400 | V | |
| Collector-Base Voltage | | V _{CBO} | 700 | V | |
| Collector-Emitter Vo | oltage (V _{BE} =0 |) | V _{CES} | 700 | V |
| Emitter Base Voltag | e | | V _{EBO} | 9 | V |
| Collector Current | | Continuous | I _C | 1.2 | А |
| | | Peak (1) | I _{CM} | 2.4 | А |
| | T 05%0 | TO-126 | | 1.4 | W |
| Device Disationation | T _A =25°C | TO-92 | | 1.1 | W |
| Power Dissipation | T 05°0 | TO-126 | PD | 20 | W |
| | T _C =25°C | TO-92 | | 1.5 | W |
| Junction Temperatu | ire | | TJ | +150 | °C |
| Storage Temperatur | re | | T _{STG} | -55 ~ +150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified.)

| | | 1 | 1 | | | | |
|--------------------------------------|-----------------------|-----------------------|--|-----|------|------|------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
| OFF CHARACTERISTICS (No | ote) | | | | | | |
| Collector-Emitter Sustaining Voltage | | V _{CEO(SUS)} | I _C =10mA , I _B =0 | 400 | | | V |
| Callester Cutoff Current | T _C =25°C | | V _{CEO} =Rated Value, | | | 1 | mA |
| Collector Cutoff Current | T _C =100°C | I _{CEO} | V _{BE(OFF)} =1.5 V | | | 5 | |
| Emitter Cutoff Current | | I _{EBO} | V _{EB} =9V, I _C =0 | | | 1 | mA |
| ON CHARACTERISTICS (Not | e) | | | | | | |
| DC Current Gain | | h _{FE1} | I _C =0.2A, V _{CE} =5V | 15 | | 30 | V |
| | | h _{FE2} | I _C =1A, V _{CE} =5V | 5 | | 30 | V |
| Collector-Emitter Saturation Voltage | | V _{CE(SAT)} | I _C =1A, I _B =0.2A | | | 0.6 | V |
| Base-Emitter Saturation Voltage | | V _{BE(SAT)} | I _C =1A, I _B =0.25A | | | 1.2 | V |
| DYNAMIC CHARACTERISTIC | s | | | | | | |
| Output Capacitance | | Сов | V _{CB} =10V, I _E =0, f=0.1MHz | | 16 | | рF |
| SWITCHING CHARACTERIS | FICS | | | | | | |
| Resistive Load (Table 1) | | | | | | | |
| Delay Time | | t _D | | | 0.05 | 0.1 | μs |
| Rise Time | | t _R | V _{CC} =125V, I _C =1A, _{B1} =I _{B2} =0.2A, | | 0.5 | 1 | μs |
| Storage Time | | ts | t _P =25µs, Duty Cycle≤1% | | 2 | 4 | μs |
| Fall Time | | t _F | | | 0.4 | 0.7 | μs |
| Inductive Load, Clamped (Ta | ble 1) | | | | | | |
| Storage Time | | t _{stg} | | | 1.7 | 4 | μs |
| Crossover Time | | t _c | $I_{C}=1A, V_{CLAMP}=300V, I_{B1}=0.2A,$ | | 0.29 | 0.75 | μs |
| Fall Time | | t _F | $V_{BE(OFF)}$ =5 V_{DC} , T _C =100°C | | 0.15 | | μs |
| Diode Forward Voltage | | V _F | I _F =0.5A | | | 1.4 | V |
| Noto: Pulso Tost: P., = 300us | |)/ | | | | | |

Note: Pulse Test: P_W = 300µs, Duty Cycle ≤ 2%.



MJE13003D-XS

1 0.5

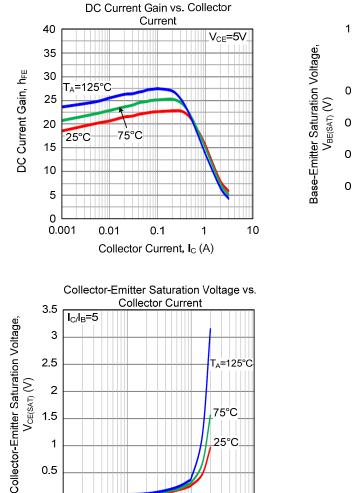
> 0 0.01

0.1

Collector Current, I_C (A)

NPN SILICON TRANSISTOR

TYPICAL CHARACTERISTICS



25°C

10

1

Base-Emitter Saturation Voltage vs. Collector Current 1.2 $I_{C}/I_{B}=5$ 1 0.8 T_A=25°C 0.6 75°C 125°C 0.4 0.2 0 └ 0.01 0.1 1 10 Collector Current, I_C (A)

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